PAN	JIT
	SEMI CONDUCTOR

Unit: inch(mm)

0.01(0.25)

0.009(0.22)

67(1.70) 59(1.50)

0.051(1.30)

.006(0.15) MAX

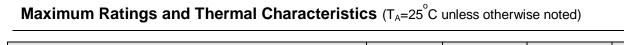
G1

0.057(1.45) MAX

#### **PJS6600 30V Complementary Enhancement Mode MOSFET – ESD Protected** SOT-23 6L Voltage 30 / -30V Current 1.6 /-1.1A **Features** .119(3.00 Advanced Trench Process Technology 0.075(1.90) • Specially Designed for Switch Load, PWM Application, etc. • ESD Protected 2KV HBM Lead free in compliance with EU RoHS 2011/65/EU 0.020(0.50) directive • Green molding compound as per IEC61249 Std. -(Halogen Free)

### **Mechanical Data**

- Case: SOT-23 6L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0005 ounces, 0.014 grams •
- Marking: SC0



PARAMETER	SYMBOL	N-Ch LIMIT	P-Ch LIMIT	UNITS	
Drain-Source Voltage		V <sub>DS</sub>	30	-30	V
Gate-Source Voltage		$V_{GS}$	<u>+</u> 8	<u>+</u> 8	V
Continuous Drain Current	I <sub>D</sub>	1.6	-1.1	А	
Pulsed Drain Current (Note 4)		I <sub>DM</sub>	6.4	-4.4	А
	T <sub>a</sub> =25°C	5	1.25		W
Power Dissipation	Derate above 25°C	P <sub>D</sub>	1	mW/°C	
Operating Junction and Storage Tem	T <sub>J</sub> ,T <sub>STG</sub>	-55~150		°C	
Typical Thermal resistance					
- Junction to Ambient (Note 3)		$R_{ extsf{ heta}JA}$	100		°C/W



## N-Channel Electrical Characteristics (T<sub>A</sub>=25<sup>°</sup>C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static	•		•	•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.5	0.78	1.3	V
Drain-Source On-State Resistance		V <sub>GS</sub> =4.5V, I <sub>D</sub> =1.6A	-	145	200	
	R <sub>DS(on)</sub>	V <sub>GS</sub> =2.5V, I <sub>D</sub> =1.1A	-	185	270	mΩ
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =0.2A	-	330	570	-
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =30V, $V_{GS}$ =0V	-	0.01	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 8V, V <sub>DS</sub> =0V	-	1.4	<u>+</u> 10	uA
Dynamic (Note 5)						
Total Gate Charge	$Q_g$		-	1.5	-	
Gate-Source Charge	$Q_gs$	V <sub>DS</sub> =15V, I <sub>D</sub> =1.6A, V <sub>GS</sub> =4.5V <sup>(Note 1,2)</sup>	-	0.3	-	nC
Gate-Drain Charge	$Q_gd$	V <sub>GS</sub> =4.5V	-	0.3	-	
Input Capacitance	Ciss	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V,	-	93	-	
Output Capacitance	Coss		-	19	-	pF
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	6	-	
Turn-On Delay Time	td <sub>(on)</sub>		-	6.4	-	
Turn-On Rise Time	tr	$V_{DD}$ =15V, I <sub>D</sub> =1.6A, $V_{GS}$ =4.5V, $R_{G}$ =6 $\Omega$ <sup>(Note 1.2)</sup>	-	33	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	37	-	ns
Turn-Off Fall Time	tf	KG=017	-	32	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>		-	-	1.0	А
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 1.0A, V <sub>GS</sub> =0V	-	0.81	1.2	V

NOTES :

- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics.
- 3. ReJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing



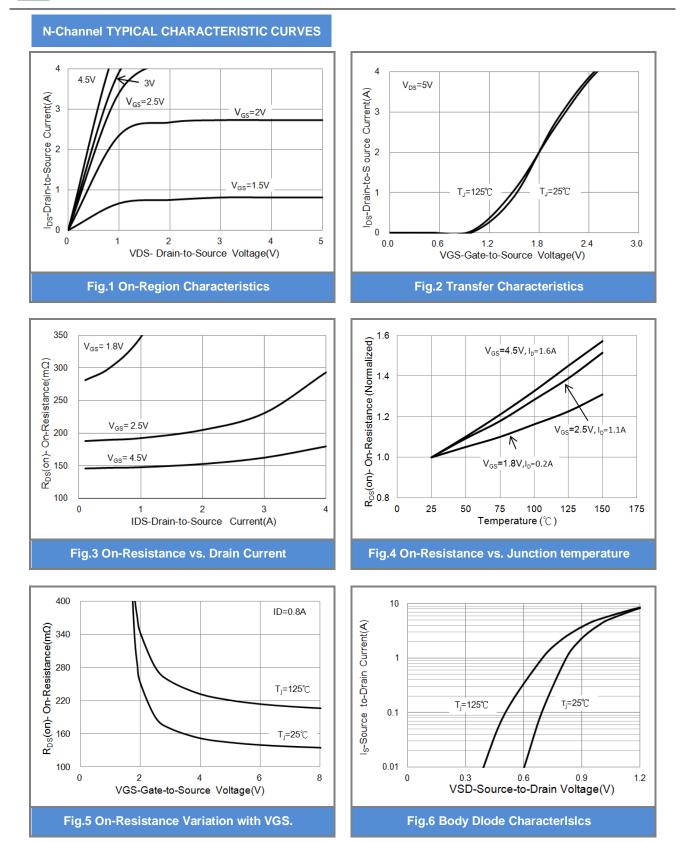
## **P-Channel Electrical Characteristics** ( $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static		Γ	1	1		1
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	$V_{GS}$ =0V, $I_{D}$ =-250uA	-30	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=-250$ uA	-0.5	-0.98	-1.3	V
Drain-Source On-State Resistance		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-1.1A	-	293	370	
	R <sub>DS(on)</sub>	V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-0.5A	-	387	540	mΩ
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-0.1A	-	750	970	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =-30V, $V_{GS}$ =0V	-	-0.01	-1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 8V, V <sub>DS</sub> =0V	-	<u>+</u> 3.4	<u>+</u> 10	uA
Dynamic (Note 5)						
Total Gate Charge	Qg		-	1.6	-	
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =-15V, $I_{D}$ =-1.1A,	-	0.5	-	nC
Gate-Drain Charge	$Q_gd$	V <sub>GS</sub> =-4.5V <sup>(Note 1,2)</sup>	-	0.3	-	
Input Capacitance	Ciss		-	125	-	
Output Capacitance	Coss	$V_{DS}$ =-15V, $V_{GS}$ =0V,	-	22	-	pF
Reverse Transfer Capacitance	Crss	f=1.0MHZ	-	6	-	
Turn-On Delay Time	td <sub>(on)</sub>		-	11	-	
Turn-On Rise Time	tr	$V_{DD}$ =-15V, I <sub>D</sub> =-1.1A, $V_{GS}$ =-4.5V, $R_{G}$ =6 $\Omega$ <sup>(Note 1,2)</sup>	-	51	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	65	-	ns
Turn-Off Fall Time	tf	K <sub>G</sub> =012	-	46	-	
Drain-Source Diode						
Maximum Continuous Drain-Source		I <sub>S</sub>			-1.0	А
Diode Forward Current	IS		-	-		
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =-1.0A, V <sub>GS</sub> =0V	-	-0.9	-1.2	V

NOTES :

- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics.
- 3. RoJA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
- 4. The maximum current rating is package limited.
- 5. Guaranteed by design, not subject to production testing.

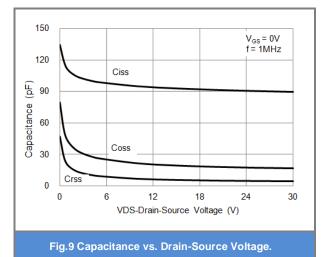


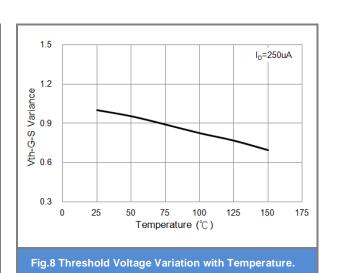


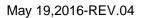


N-Channel TYPICAL CHARACTERISTIC CURVES

Fig.7 Gate-Charge Characteristics









P-Channel TYPICAL CHARACTERISTIC CURVES 4 4 V<sub>DS</sub>=-5V -4 5V . 3V -I<sub>DS</sub>-Drain-to-S ource Current(A) -I<sub>DS</sub>-Drain-to-Source Current(A) V<sub>GS</sub>=-2.5V V<sub>GS</sub>=-2V T**J=125℃** T\_=25℃ V<sub>GS</sub>=-1.5V 2 3 4 -VDS- Drain-to-Source Voltage(V) 0 1 5 0.0 0.6 1.2 1.8 2.4 3.0 -VGS-Gate-to-Source Voltage(V) **Fig.1 On-Region Characteristics Fig.2 Transfer Characteristics** 1000 1.6 R<sub>DS</sub>(on)- On-Resistance (Normalized) V<sub>GS</sub>= -1.8V R<sub>DS</sub>(on)- On-Resistance(mΩ) 800 1.4 V<sub>GS</sub>=-4.5V, I<sub>D</sub>=-1.1A V<sub>GS</sub>=-2.5V, I<sub>D</sub>=-0.5A 600 1.2 V<sub>GS</sub>=-1.8V, I<sub>D</sub>=-0.1A V<sub>GS</sub>= -2.5V 400 1.0 V<sub>GS</sub>= -4.5V 200 0.8 75 100 Temperature (℃) 0 2 2 0 25 **50** 125 150 175 1 1 -IDS-Drain-to-Source Current(A) Fig.3 On-Resistance vs. Drain Current Fig.4 On-Resistance vs. Junction temperature 10 900 ID=-0.55A -Is-Source to-Drain Current(A) R<sub>DS</sub>(on)- On-Resistance(mΩ) 00 002 002 1 . Ti=125℃ T<sub>j</sub>=125℃ Tj=25℃ 0.1 Tj=25℃ 0.01 100 0 2 4 -VGS-Gate-to-Source Voltage(V) 0 0.3 0.6 0.9 1.2 8 6 -VSD-Source-to-Drain voltage(V) Fig.5 On-Resistance Variation with VGS. **Fig.6 Body Dlode CharacterIsIcs** 



#### P-Channel TYPICAL CHARACTERISTIC CURVES

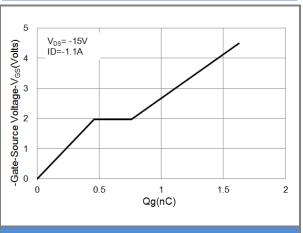
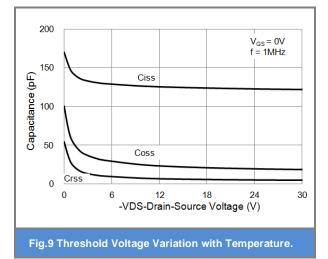
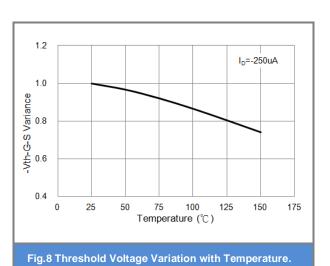


Fig.7 Gate-Charge Characteristics







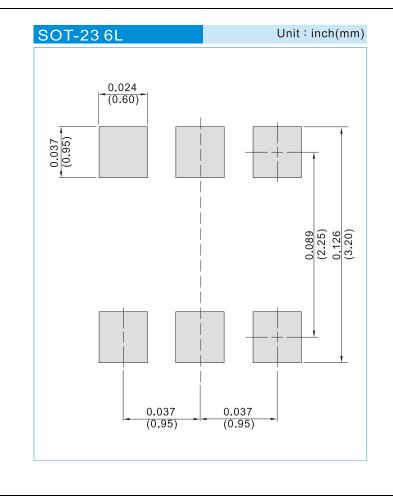




### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJS6600_S1_00001	SOT-23 6L	3K pcs / 7" reel	SC0	Halogen free
PJS6600_S2_00001	SOT-23 6L	10K pcs / 13" reel	SC0	Halogen free

### MOUNTING PAD LAYOUT







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